# N-Channel Enhancement Mode Power MOSFET

## Description

The GT130N10D3A uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

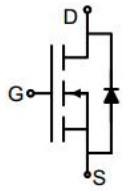
AEC-Q101 Qualified

## General Features

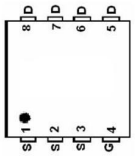
- $V_{DS}$ 100V
- $I_D$ (at $V_{GS}$ = 10V) 52A
- $R_{DS(ON)}$ (at $V_{GS}$ = 10V) < 12.5mΩ
- 100% Avalanche Tested
- RoHS Compliant

## Application

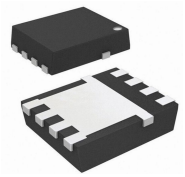
- Power switch
- DC/DC converters




Schematic diagram




pin assignment



DFN3X3-8L

## Ordering Information

| Device | Package | Marking | Packaging |
|---|---|---|---|
| GT130N10D3A | DFN3X3-8L | GT130N10 | 3000pcs/Reel |

## Absolute Maximum Ratings $T_C$ = 25ºC, unless otherwise noted

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Drain-Source Voltage | $V_{DS}$ | 100 | V |
| Continuous Drain Current | $I_D$ | 52 | A |
| Pulsed Drain Current (note1) | $I_{DM}$ | 208 | A |
| Gate-Source Voltage | $V_{GS}$ | ±20 | V |
| Power Dissipation | $P_D$ | 71 | W |
| Single pulse avalanche energy （note2） | $E_{AS}$ | 56 | mJ |
| Operating Junction and Storage Temperature Range | $T_J$, $T_{stg}$ | -55 To 150 | ºC |

## Thermal Resistance

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Thermal Resistance, Junction-to-Ambient | $R_{thJA}$ | 50 | ºC/W |
| Maximum Junction-to-Case | $R_{thJC}$ | 1.76 | ºC/W |

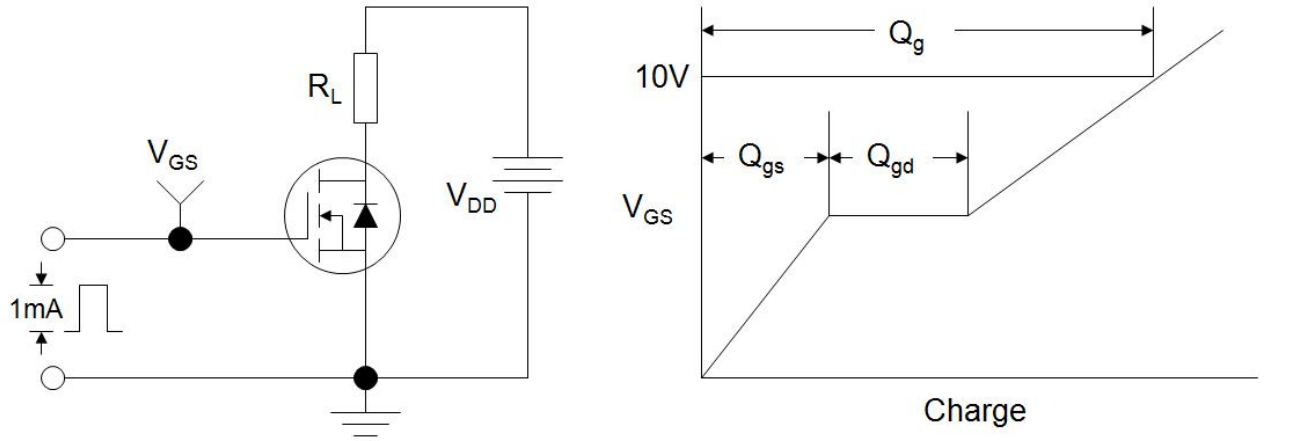
**Specifications** $T_J$ = 25ºC, unless otherwise noted

| Parameter | Symbol | Test Conditions | Value | | | Unit |
|---|---|---|---|---|---|---|
| | | | Min. | Typ. | Max. | |
| **Static Parameters** | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}$ = 0V, $I_D$ = 250μA | 100 | -- | -- | V |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 100V, $V_{GS}$ = 0V | -- | -- | 1 | μA |
| Gate-Source Leakage | $I_{GSS}$ | $V_{GS}$ = ±20V | -- | -- | ±100 | nA |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250μA | 2.0 | 3.0 | 4.0 | V |
| Drain-Source On-Resistance | $R_{DS(on)}$ | $V_{GS}$ = 10V, $I_D$ = 20A | -- | 10.6 | 12.5 | mΩ |
| Forward Transconductance | $g_{FS}$ | $V_{GS}$ = 5V, $I_D$ = 20A | -- | 35 | -- | S |
| **Dynamic Parameters** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{GS}$ = 0V, $V_{DS}$ = 50V, f = 1.0MHz | -- | 1254 | -- | pF |
| Output Capacitance | $C_{oss}$ | | -- | 461 | -- | |
| Reverse Transfer Capacitance | $C_{rss}$ | | -- | 10 | -- | |
| Total Gate Charge | $Q_g$ | $V_{DD}$ = 50V, $I_D$ = 20A, $V_{GS}$ = 10V | -- | 18 | -- | nC |
| Gate-Source Charge | $Q_{gs}$ | | -- | 6 | -- | |
| Gate-Drain Charge | $Q_{gd}$ | | -- | 3 | -- | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}$ = 50V, $I_D$ = 20A, $R_G$ = 3Ω | -- | 7 | -- | ns |
| Turn-on Rise Time | $t_r$ | | -- | 3 | -- | |
| Turn-off Delay Time | $t_{d(off)}$ | | -- | 15 | -- | |
| Turn-off Fall Time | $t_f$ | | -- | 2 | -- | |
| **Drain-Source Body Diode Characteristics** | | | | | | |
| Continuous Body Diode Current | $I_S$ | $T_C$ = 25ºC | -- | -- | 52 | A |
| Body Diode Voltage | $V_{SD}$ | $T_J$ = 25ºC, $I_{SD}$ = 20A, $V_{GS}$ = 0V | -- | -- | 1.2 | V |
| Reverse Recovery Charge | Qrr | $I_F$ = 20A, $V_{GS}$ = 0V di/dt=500A/us | -- | 120 | -- | nC |
| Reverse Recovery Time | Trr | | -- | 23 | -- | ns |

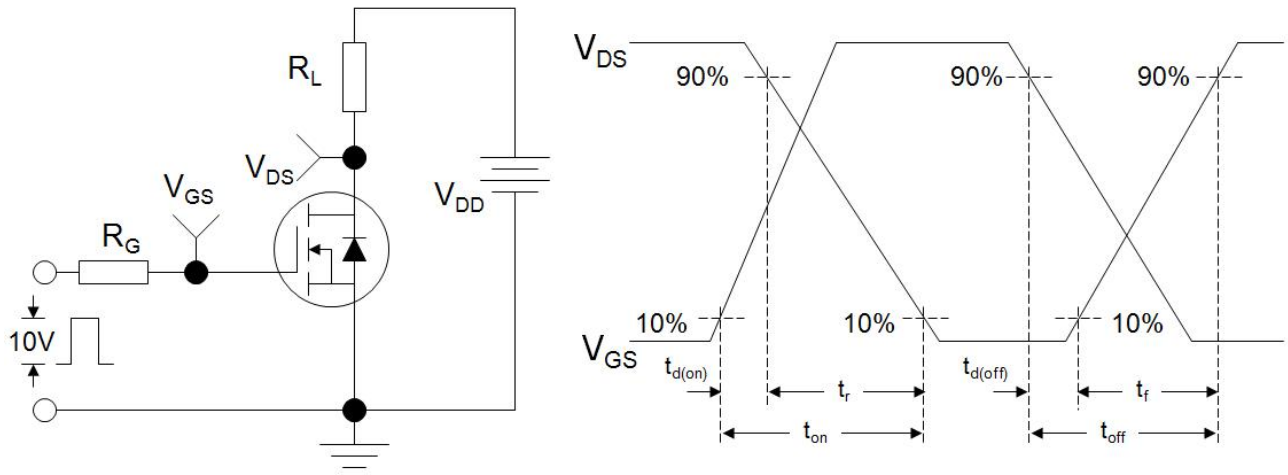
**Notes**

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : Tj=25℃ ,VDD=50V,VGS=10V,L=0.5mH,Rg=25Ω
   The table shows the minimum avalanche energy, which is 156mJ when the device is tested until failure
3. Identical low side and high side switch with identical $R_G$

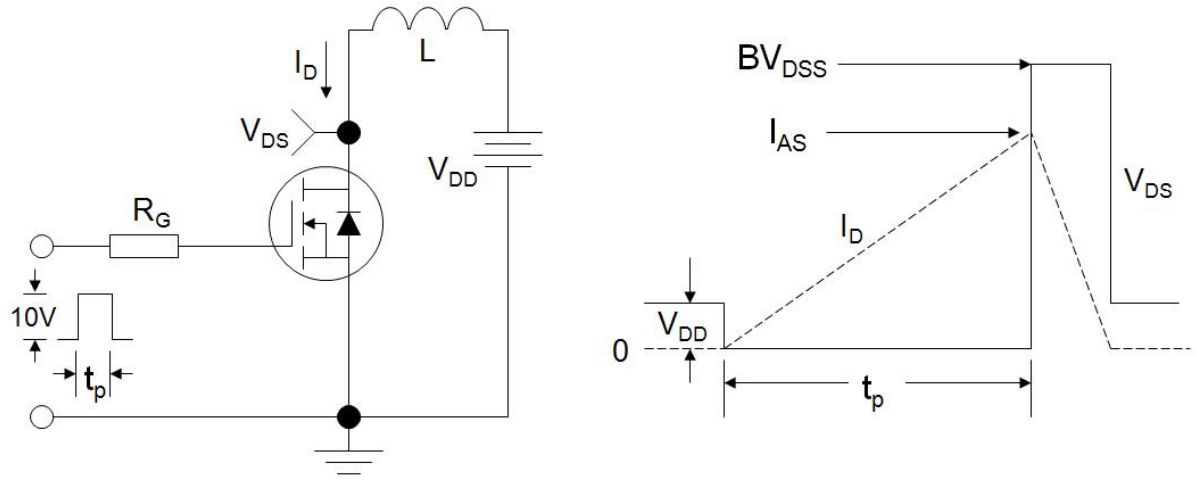
**Gate Charge Test Circuit**




**Switch Time Test Circuit**




**EAS Test Circuit**



## Typical Characteristics $T_J$ = 25ºC, unless otherwise noted

**Figure 1. Output Characteristics**

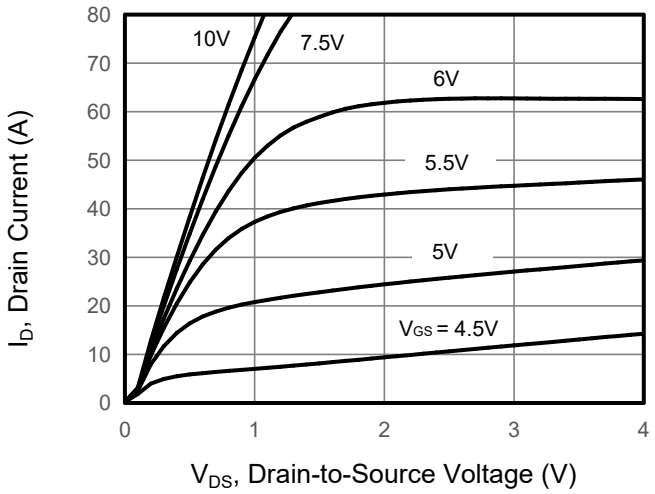



**Figure 2. Transfer Characteristics**

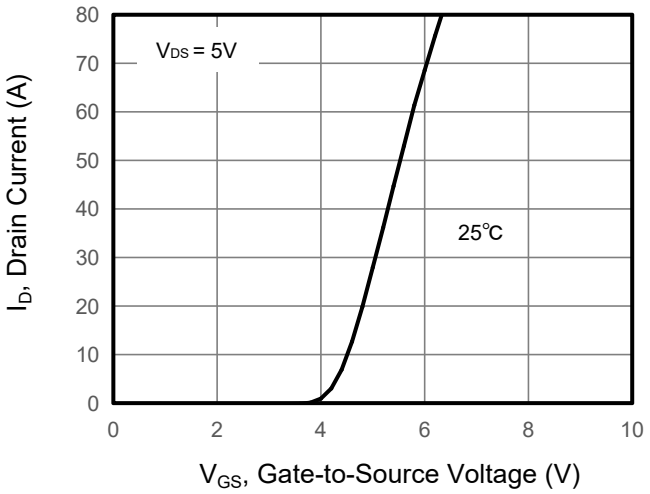



**Figure 3. Drain Source On Resistance**

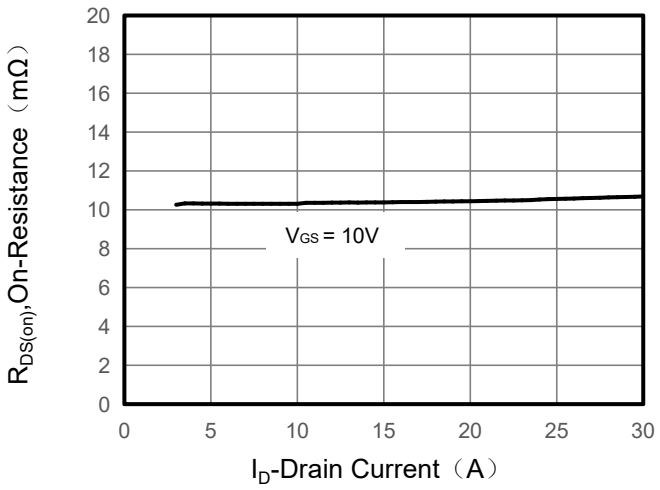



**Figure 4. Gate Charge**

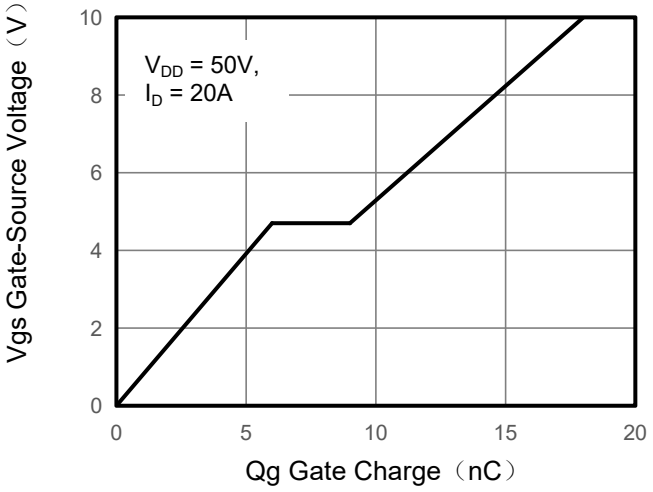



**Figure 5. Capacitance**

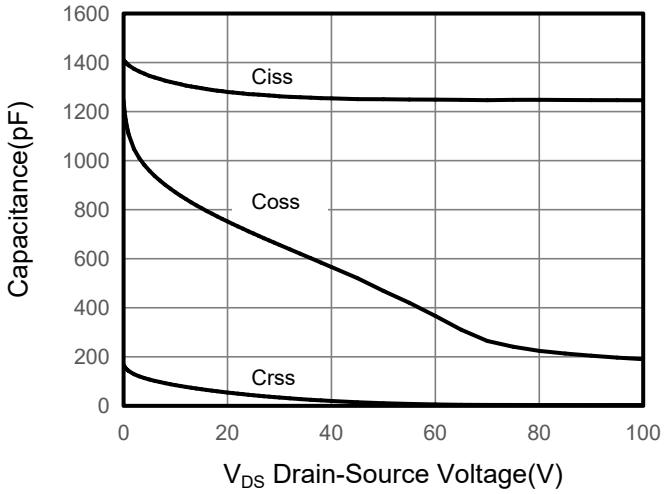
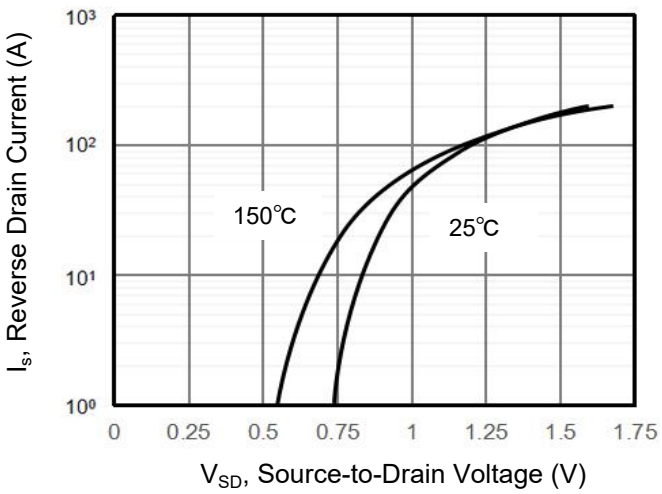



**Figure 6. Source-Drain Diode Forward**



**Typical Characteristics** $T_J$ = 25ºC, unless otherwise noted

**Figure 7. Drain-Source On-Resistance**

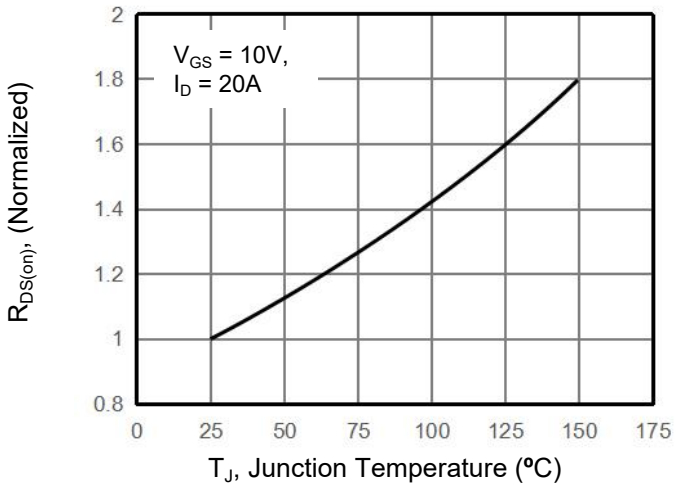



**Figure 8. Safe Operation Area**

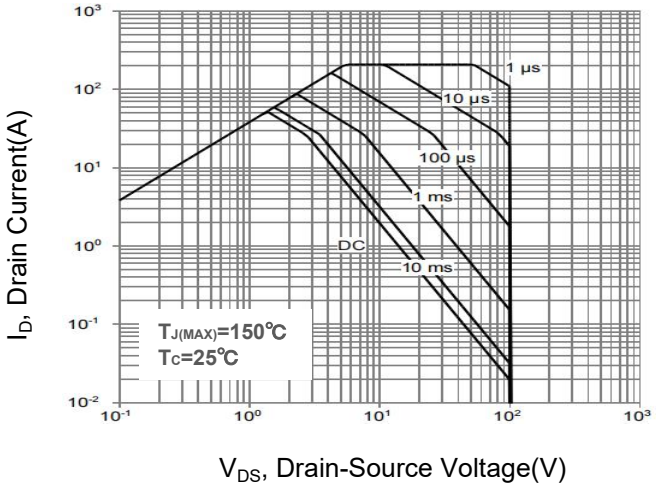
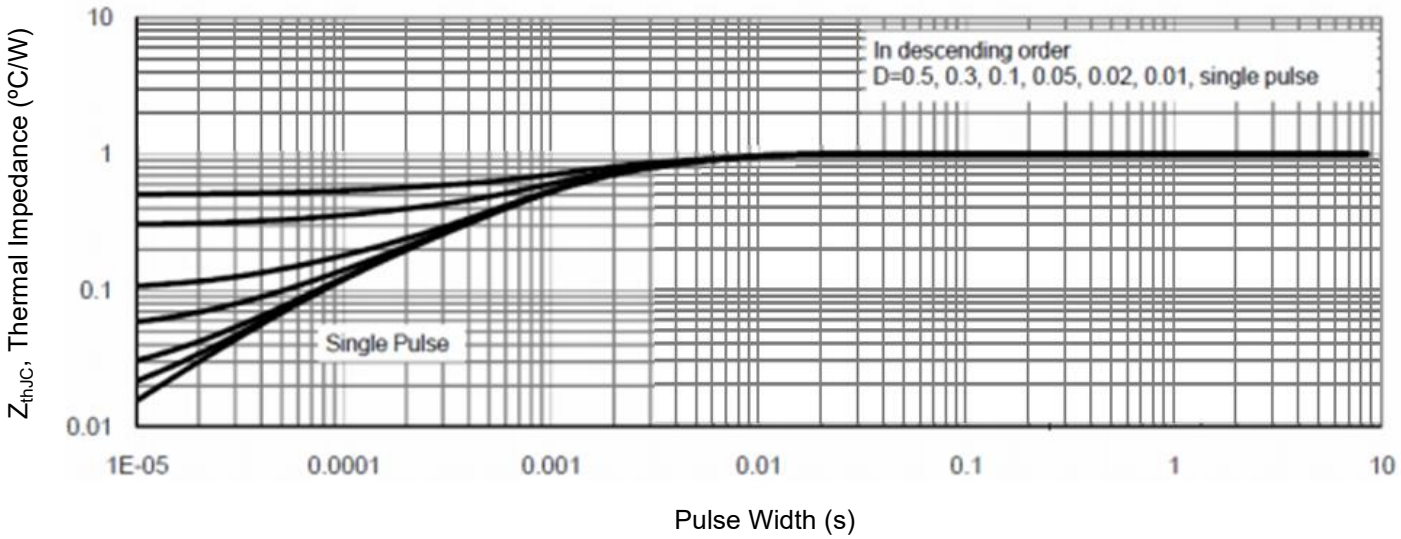
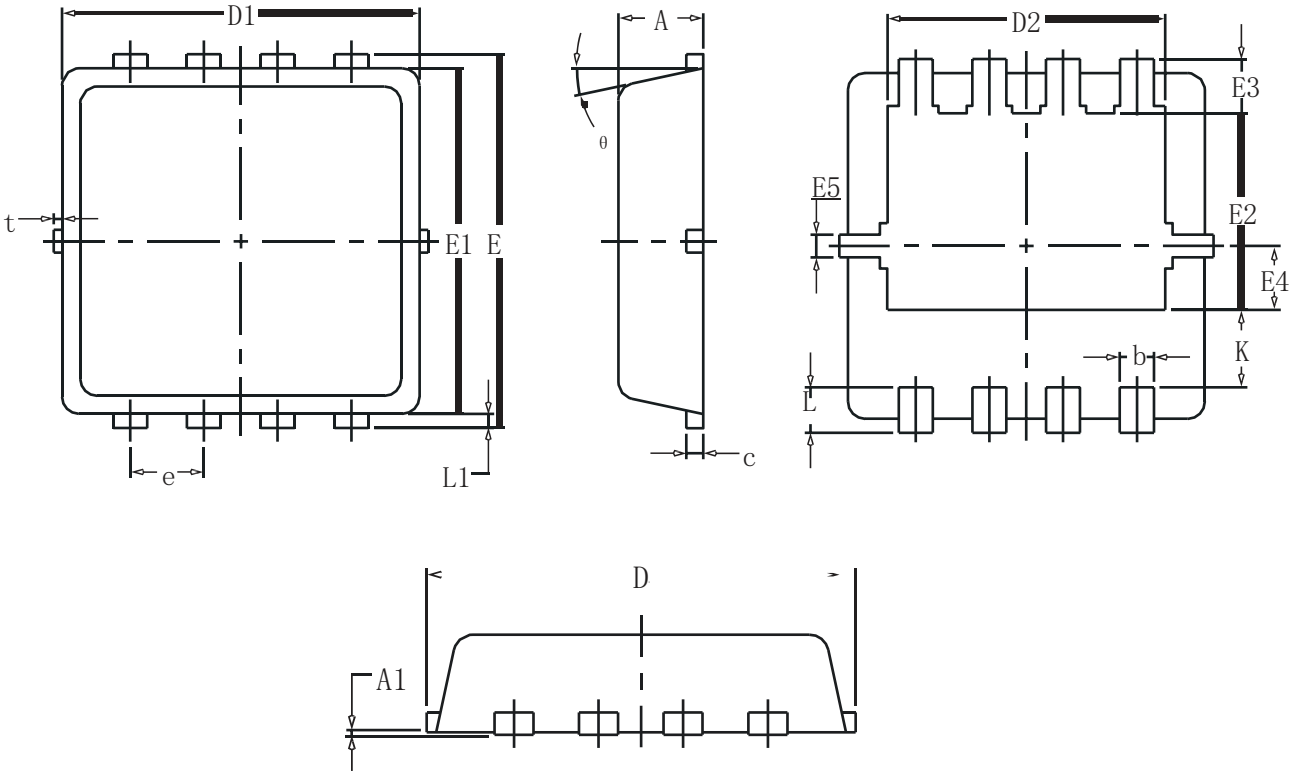



**Figure 9. Normalized Maximum Transient Thermal Impedance**



## DFN3x3-8L Package Information




| SYMBOL | COMMON | | |
|---|---|---|---|
| | MM | | |
| | MIN | NOM | MAX |
| A | 0.70 | 0.75 | 0.85 |
| A1 | - | - | 0.05 |
| b | 0.20 | 0.30 | 0.40 |
| c | 0.10 | 0.152 | 0.25 |
| D | 3.15 | 3.30 | 3.45 |
| D1 | 3.00 | 3.15 | 3.25 |
| D2 | 2.29 | 2.45 | 2.65 |
| E | 3.15 | 3.30 | 3.45 |
| E1 | 2.90 | 3.05 | 3.20 |
| E2 | 1.54 | 1.74 | 1.94 |
| E3 | 0.28 | 0.48 | 0.65 |
| E4 | 0.37 | 0.57 | 0.77 |
| E5 | 0.10 | 0.20 | 0.30 |
| e | 0.60 | 0.65 | 0.70 |
| K | 0.59 | 0.69 | 0.89 |
| L | 0.30 | 0.40 | 0.50 |
| L1 | 0.06 | 0.125 | 0.20 |
| t | 0 | 0.075 | 0.13 |
| θ | 10° | 12° | 14° |